



DCR4500A42

(LN41637)

Phase Control Thyristor

Replaces DS5942-7 DS5942-8 March 2022

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR4500A42* DCR4500A40 DCR4500A36	4200 4000 3600	Tvj = -40°C to 125°C, IDRM = IRRM = 300mA, VDRM, VRRM tp = 10ms VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

KEY PARAMETERS

V DRM	4200V
IT(AV)	4450A
Ітѕм	60000A
dV/dt*	2000V/μs
dl/dt	500A/μs

^{*} Higher dV/dt selections are available on request

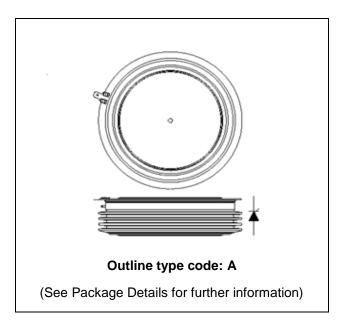


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR4500A42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

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^{*4100}V @ -40°C, 4200V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	4450	А
IT(RMS)	RMS value	-	6990	А
lτ	Continuous (direct) on-state current	-	6270	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	60.0	kA
l²t	I2t for fusing	V _R = 0	18.0	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
		Double side cooled	DC	-	6.0	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side and a	Anode DC	-	10.4	°C/kW
		Single side cooled	Cathode DC	-	14.9	°C/kW
D. C.	The second secon	Clamping force 83kN	Double side	-	1.0	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			74	91	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Тур.	Max.	Units
l===//===	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C		300	mA
IRRM/IDRM	Peak reverse and oir-state current	At 50% VRRM/VDRM, Tcase = 125°C	20	-	mA

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
Vтм	Instantaneous forward voltage	At 4000A peak, T _j = 125°C		1.30	1.45	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	200	A/µs
ui/ut	Nate of fise of off-state current	Gate source 30V, 10Ω tr < 0.5μ s, $T_j = 125$ °C	Non-repetitive	-	500	A/µs
V T(TO)	Threshold voltage - Low level 500A to 3400A at Tcase = 125°C		-	0.81	٧	
V T(TO)	Threshold voltage - High level 3400A to 9000A at Tcase = 125°C		-	0.98	V	
	On-state slope resistance - Low level 500A to 3400A at Tcase = 125°C		-	0.17	mΩ	
ľτ	On-state slope resistance - High level	3400A to 9000A at Tcase = 125°C		-	0.12	mΩ
tgd	Delay time	$V_D = 67\%$ V _{DRM} , gate source $t_r = 0.5\mu s$, $T_j = 25$ °C	e 30V, 10Ω	-	3	μs
tq	Turn-off time	IT = 5000A, Tj = 125°C, VR = dI/dt = 5A/µs, dVpR/dt = 20V		-	900	μs
Qs	Stored charge	Iτ = 1700A, Tj = 125°C, dl/dt = 1A/μs,		2570	5350	μC
Irr	Reverse recovery current	$V_R \sim 1700V$, $C_S = 1\mu F$, $R_S = 63\Omega$		42	68	А
lι	Latching current $T_j = 25^{\circ}C, V_D = 5V$		-	3	Α	
Ін	Holding current	Tj = 25°C, Rg-κ = ∞, I _{TM} = 50	0Α, Iτ = 5Α	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	٧
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
IGD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

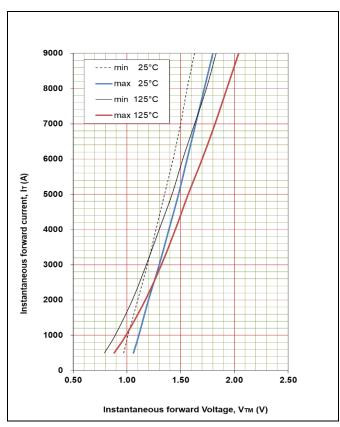


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.090451

B = 0.121408

C = 0.000109

D = -0.001368

These values are valid for T_j = 125°C for I_T 500A to 9000A

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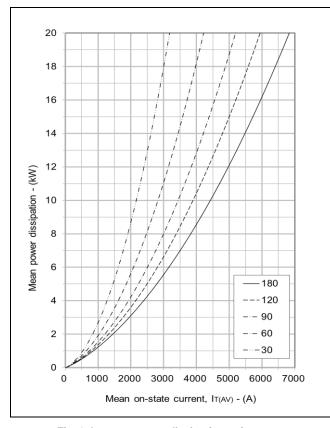


Fig. 3 On-state power dissipation - sine wave

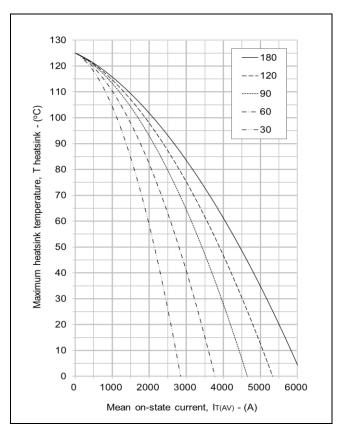


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

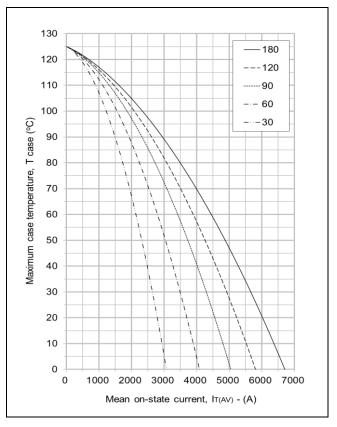


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

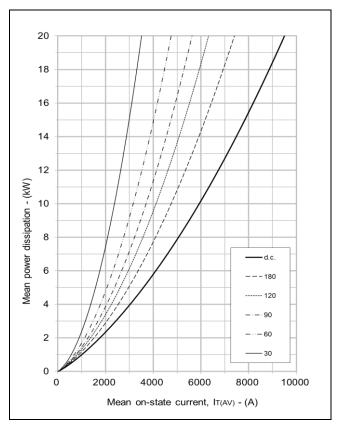


Fig. 6 On-state power dissipation - rectangular wave

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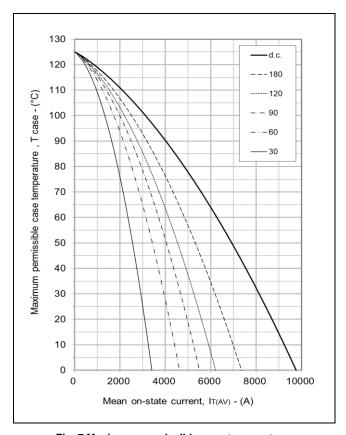
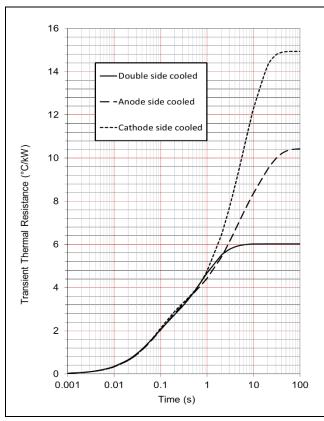


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



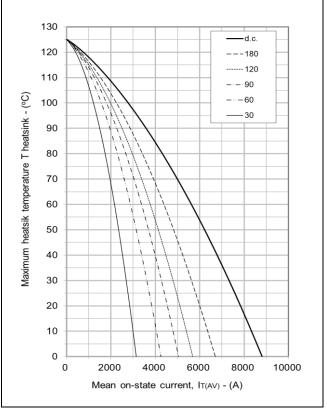


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	3.015	1.049	0.984	0.984
cooled	Ti(s)	0.704	1.905	0.059	0.059
Anode side	Ri(°C/kW)	3.156	4.093	1.557	1.624
cooled	Ti(s)	2.690	13.792	0.059	0.206
Cathode side	Ri(°C/kW)	7.077	3.483	1.746	2.634
cooled	Ti(s)	6.649	8.436	1.762	0.081

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

Double side cooling				Aı	node
	ΔZ_{th}	(z)			
θ°	sine.	rect.		θ°	si
180	0.44	0.31		180	0
120	0.49	0.43		120	0
90	0.55	0.49		90	0
60	0.60	0.55		60	0
30	0.64	0.61		30	0
15	0.66	0.64		15	0

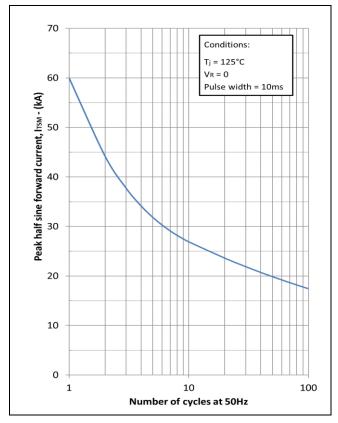
	Αı	Anode Side Cooling		
		ΔZ_t	_h (z)	
]	θ°	sine.	rect.	
	180	0.42	0.30	
1	120	0.47	0.41	
	90	0.52	0.46	
	60	0.57	0.52	
I	30	0.61	0.58	
1	15	0.62	0.61	

Cathode Sided Cooling				
	ΔZ	th (z)		
θ°	sine.	rect.		
180	0.42	0.30		
120	0.47	0.41		
90	0.52	0.46		
60	0.57	0.52		
30	0.60	0.58		
15	0.62	0.60		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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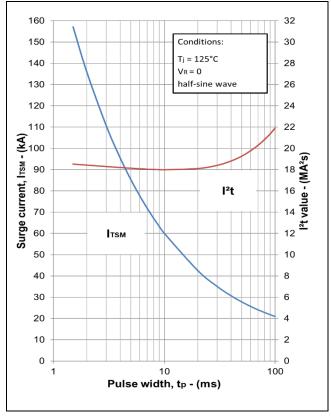


Fig. 10 Multi-cycle surge current

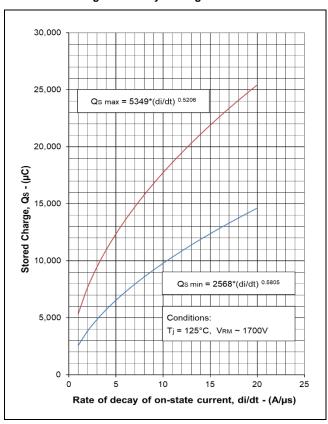


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

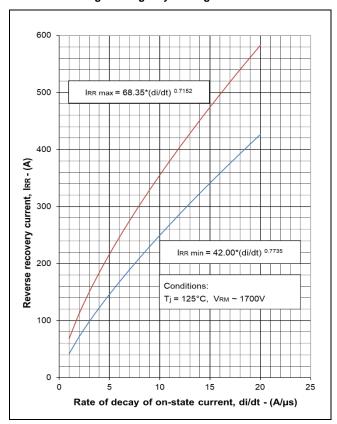


Fig. 13 Reverse recovery current

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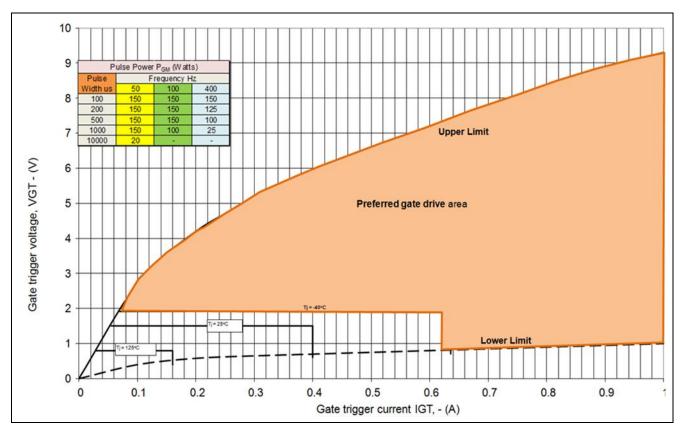


Fig.14 Gate characteristics

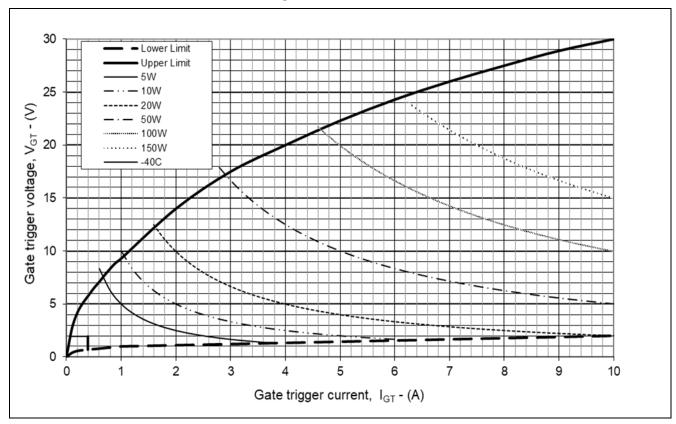


Fig. 15 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

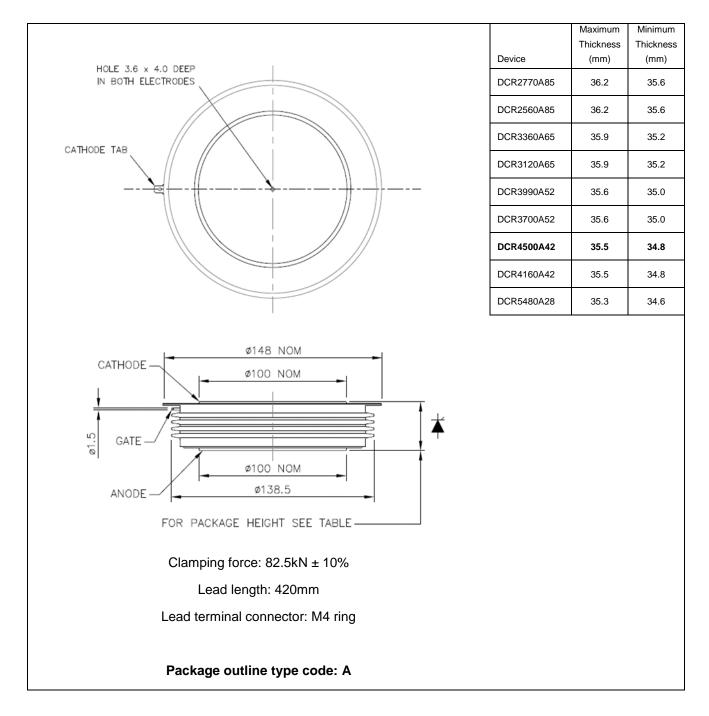


Fig. 16 Package outline

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